

/ Descriptions

DFN1006-2L

Silicon Diode in a DFN1006-2L Plastic Package.

/ Features

Fast switching diodes, HF Product.

/ Applications

Small signal diode.

/ Equivalent Circuit



/ Pinning



PIN1:Anode

PIN2:Cathode

/ Marking

Marking	HA2
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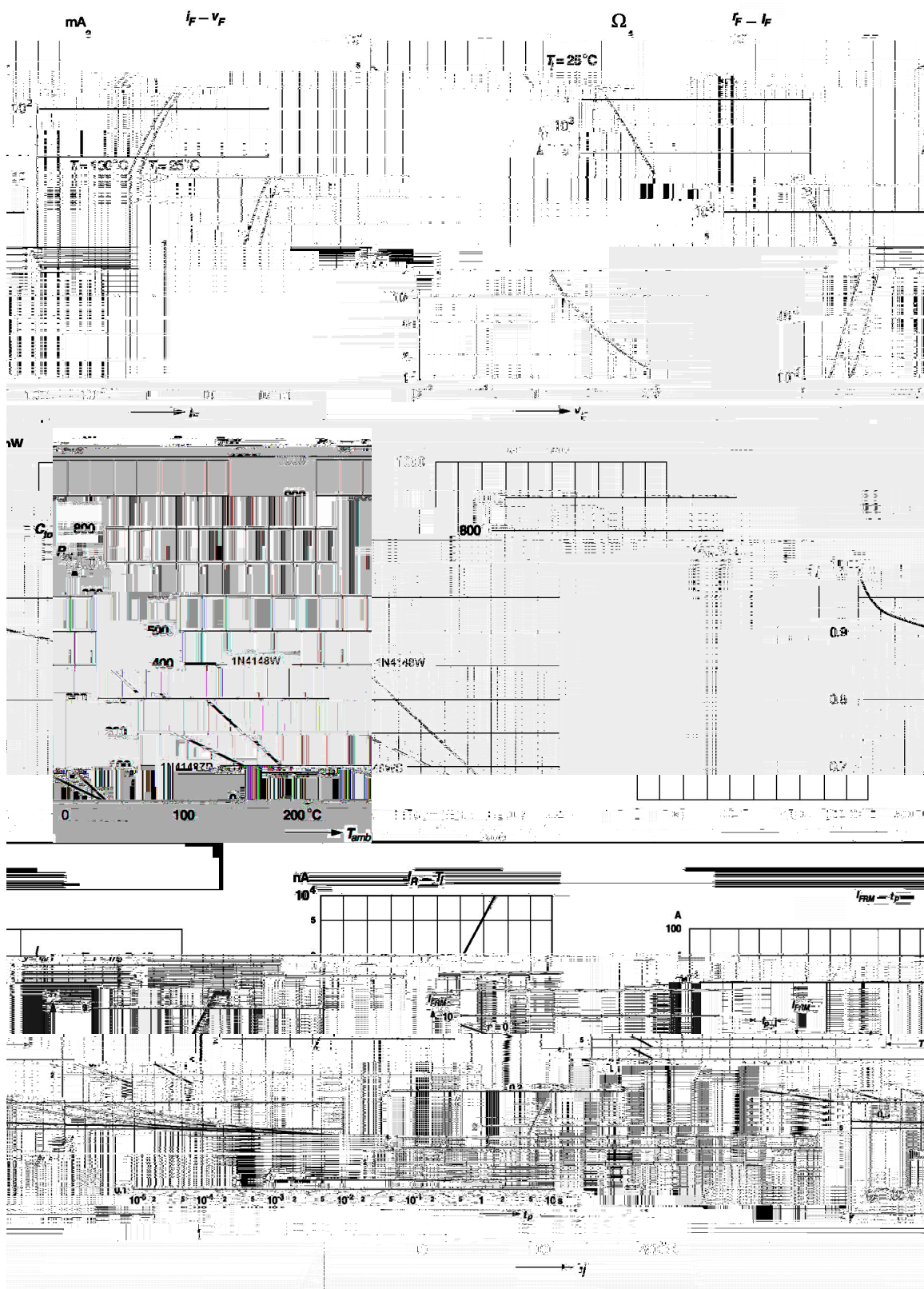
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Reverse Voltage	V_R	80	V
Peak Reverse Voltage	V_{RM}	100	V
Rectified Current (Average)	I_O	215	mA
Forward Continuous Current	I_{FM}	300	mA
repetitive peak forward current	I_{FRM} ($t_p \leq 0.5 \mu s; \delta \leq 0.25$)	500	mA
Surge Forward Current	$I_{FSM} \quad t=1.0\mu s \sim$	4.0	A
	$I_{FSM} \quad t=1.0s \sim$	1.0	A
Power Dissipation	P_{tot}	250	mW
Operating and Storage Temperature Range	T_j, T_{stg}	-55° +150	
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	500	/W

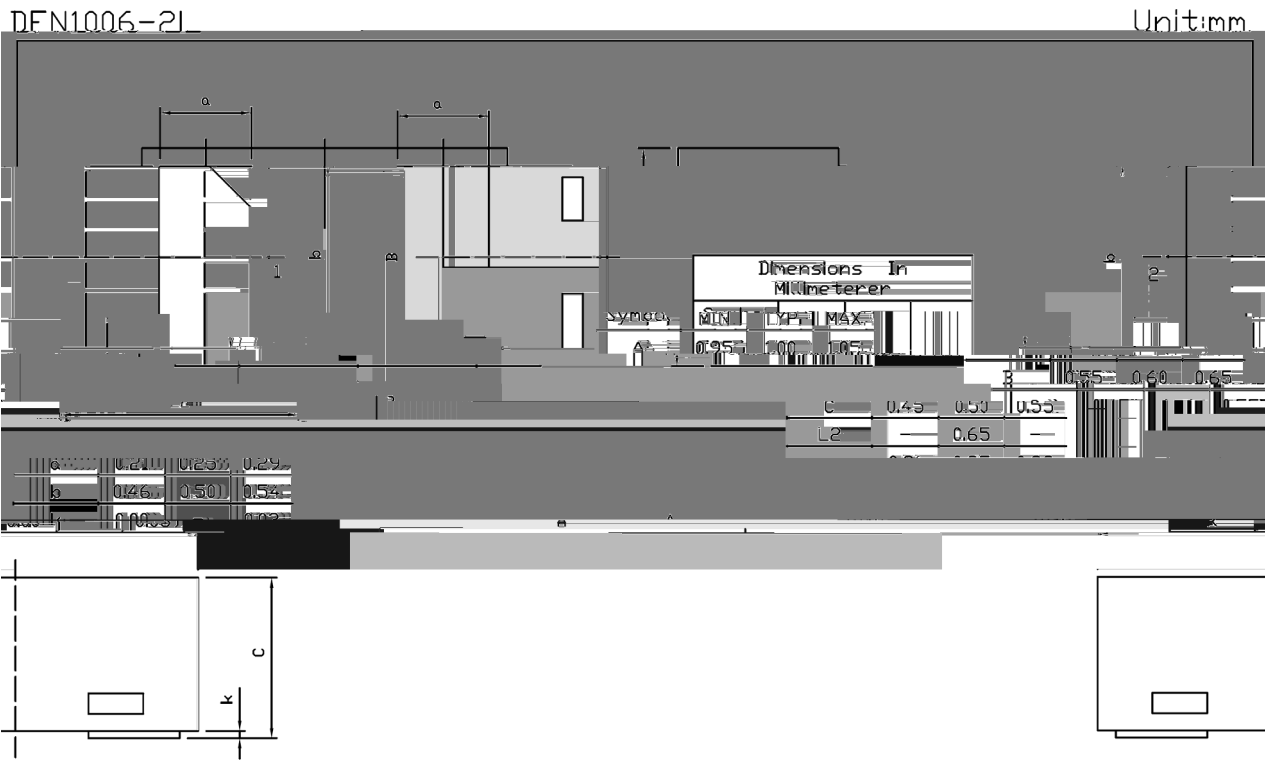
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	$I_F=1.0mA$			715	mV
		$I_F=10mA$			855	mV
		$I_F=50mA$			1.0	V
		$I_F=150mA$			1.25	V
Instantaneous Reverse Current	I_R	$V_R=20V$			25	nA
		$V_R=75V$			5	μA
		$V_R=20V \quad T_j=150N$			50	μA
Capacitance	C_{tot}	$V_F=V_R=0V$			4	pF
Reverse Recovery Time	t_{rr}	$I_F=10mA \quad V_R=6.0V$ $I_R=1mA \quad R_L=100\Omega$			4	ns
Voltage Rise when Switching On tested	V_{fr}	$t_p=0.1\mu s \quad f_p=5to100kHz$ Time<30ns			2.5	V
Total Capacitance	C_T	$V_R=0 \quad f=1.0MHz$			5.0	pF

/ Electrical Characteristic Curve



/ Package Dimensions



Rev.01 202108

/ Marking Instructions



H

A2

Note:

H: Company Code

A2: Product Type Code

